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PATENT AND TRADEMARK OFFICE

**REQUEST FOR CERTIFICATE OF
CORRECTION PURSUANT TO
37 C.F.R. § 1.322**

Docket Number:

10191/1466

Conf. No.:

4295

Application Number

09/581,663

Filing Date

August 3, 2000

Examiner

Ahmed, Shamim

Art Unit

1765

Patent Number

7,052,623

Issue Date

May 30, 2006

Invention Title

**METHOD FOR PROCESSING SILICON
USING ETCHING PROCESSES**

Inventor(s)

BECKER, Volker et al.

Address to:

Commissioner For Patents
P. O. Box 1450
Alexandria, VA 22313-1450

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to : Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on:

Date: 4/3/07

Signature: R. Hannan

Sir:

We have compared the above patent with the application as filed and have found an error in the printing of the patent. We respectfully request that the enclosed Certificate of Correction on Form PTO-1050 be issued correcting the mistake set forth therein under authority of 35 U.S.C. §254. The exact column and line number where the error occurs in the patent is listed on the enclosed certificate.

The error that appears in this patent is a Patent Office error and no fee is believed required. However, if necessary, please charge any fee or credit any overpayment to Deposit Account No. 11-0600.

Dated: 4/3/07

By:

Gerard A. Messina Reg. No. 22,490

KENYON & KENYON LLP
One Broadway
New York, New York 10004
(212) 425-7200 (telephone)
(212) 425-5288 (facsimile)

**Certificate
APR 10 2007
of Correction**

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT No. : 7,052,623

DATED : May 30, 2006

INVENTOR(S): BECKER, Volker et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1, line 24, change "Disadvantages" to --Disadvantageous--

Column 1, line 33, change "can act very" to --can act very corrosively.--

Column 3, line 12, change "...OF THE DRAWING" to --OF THE
DRAWINGS--

Column 6, line 13, change "in which the. silicon" to --in which the silicon--

Column 7, line 16, change "DE 42 41 045, and" to --DE 42 41 045, an--

Column 7, line 32, change "remain essentially" to --remain essentially
unchanged.--

Column 11, line 54, change "etching process than etching" to --etching
process then etching--

Column 12, line 40, change "layer section 912)" to --layer section (12)--

Column 16, line 18, change "is formed thermally grown silicon" to --is
formed from thermally grown silicon--

MAILING ADDRESS OF SENDER

Kenyon & Kenyon LLP
One Broadway
New York, NY 10004

NY01 1320459 v1

Patent No. 7,052,623 B1

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